Excitons with an isotropic e ective mass

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A bstract. We present a simple analytic scheme for calculating the binding energy of excitons in sem iconductors that takes full account of the existing anisotropy in the elective mass, as a complement to the qualitative treatment in most textbooks. Results obtained for excitons in gallium nitride form the basis for a discussion of the accuracy of this approach.

Zusam menfassung. Wir prasentieren ein einfaches analytisches Verfahren zur Berechnung der Bindungsenergie von Exzitonen in Halbleitern, das die vorhandene Anisotropie in der eektiven Masse vollstandig miteinbezieht, in Erganzung zu der qualitativen Betrachtung in den meisten Lehrbuchern. Ergebnisse für Exzitonen in Gallium nitrid bilden die Grundlage für eine Diskussion der Genauigkeit dieser Methode.

I. IN TRODUCTION

The traditional one-particle theory of sem iconductors as taught in undergraduate courses is that of a materialwith a nite energy gap separating the highest occupied from the lowest unoccupied electronic state. In this picture the minimum energy for an elementary excitation is that required to raise a valence band electron into the conduction band, and is thus equal to the gap E_{g} . However, the electron and the hole, which is created in the same process, need not separate com pletely and can instead form a bound pair under the in uence of their mutual Coulomb attraction [1]. Such bound electronhole pairs, which transport energy and momentum but no charge, are called excitons. They are, in fact, the truly lowest elementary excitations of a pure sem iconductor and their in uence on the optical properties of a m aterial is profound. M ost in portantly, the occurrence of excitons lowers the threshold for photon absorption to E_{a} E_{b} , where E_{b} denotes the internal binding energy of the electron-hole pair.

Because of their practical signi cance excitons feature in all textbooks on solid state physics, but the discussion is usually restricted to som e qualitative argum ents based on form al sim ilarities to the hydrogen atom problem, which is modi ed only by a dielectric constant to account for the surrounding medium and by empirical e ective masses for the electron and hole [2]. The latter are always assumed to be isotropic, but while there certainly are textbook examples such as CdS for which this condition is nearly satis ed and hydrogenic absorption series have indeed been observed [3], in most sem iconductors the anisotropy in the e ective mass is so large that it cannot be ignored in a quantitative treatm ent. In this paper we present a variational scheme for calculating the binding energy E_b of excitons in realistic materials that takes full account of the existing an isotropy. Our priority has been to maintain a universally applicable and strictly analytic approach suitable for teaching purposes.

II. VARIATIONAL EXCITON WAVEFUNCTION

M ost sem iconductors used for m odern electronic devices crystallize in the diam ond (e.g. Si, G e), zincblende (e.g. G aA s) or wurtzite (e.g. G aN) structure, for which the constant energy surfaces E (k) about the valence band m axim um and conduction band m inim um are ellipsoidal in shape, yielding distinct longitudinal electron and hole e ective m asses m_k^e and m_k^h along one principalaxis, and transverse e ective m asses m_2^e and m_2^h in the plane perpendicular to it. Here we will focus on this geom etry, although the m ethod is readily generalized. Taking the principalaxis in the z-direction, the H am iltonian for the relative m otion of the electron-hole pair is

$$H = \frac{h^{2}}{2_{?}} \frac{\theta^{2}}{\theta x^{2}} + \frac{\theta^{2}}{\theta y^{2}} \frac{h^{2}}{2_{k}} \frac{\theta^{2}}{\theta z^{2}}$$
$$\frac{e^{2}}{4_{0} p x^{2} + y^{2} + z^{2}}$$
(1)

where $_{?} = m_{?}^{e}m_{?}^{h} = (m_{?}^{e} + m_{?}^{h})$ and $_{k} = m_{k}^{e}m_{k}^{h} = (m_{k}^{e} + m_{k}^{h})$ denote the reduced transverse and longitudinale ective m ass, respectively, and is a suitable dielectric constant. The anisotropy destroys the spherical sym m etry of the hydrogen H am iltonian, yielding a wavefunction w ith a di erent characteristic localization along the principal axis and in the transverse plane. We therefore choose a generalization of the hydrogen ground-state wavefunction w ith ellipsoidal sym m etry

$$(x;y;z) = -\frac{3}{2} \exp \frac{p}{x^2 + y^2 + (z=)^2}$$
 (2)

where the two parameters and can be varied independently to control the transverse and longitudinal extension. The wavefunction, of course, becomes exact in the isotropic case $_{\rm k}$ = $_{?}$ with = 1 and 1 = a_0 m = $_{?}$, where a_0 = 0:529A denotes the Bohr radius and m is the free electron m ass, but it remains an excellent approximation even when the anisotropy is large. A wavefunction

of the type (2) was originally proposed in [4] to describe shallow donor in purity states in Si and Ge, but treated numerically and evaluated only for the mathematically distinct case < 1, re ecting the fact that the longitudinal electrons at the bottom of the conduction band in both materials. No such restriction will be made in this paper.

Given the explicit form of the wavefunction (2) the calculation of the kinetic energy is straightforward, using the substitution $z^0 = z =$ and a subsequent transform ation to spherical coordinates. We obtain

$$\frac{h^2}{2_{?}} \overset{Z}{=} \frac{\varrho^2}{\varrho x^2} d^3 r = \frac{h^2}{2_{?}} \overset{Z}{=} \frac{\varrho^2}{\varrho y^2} d^3 r$$
$$= \frac{h^2}{6_{?}} 2^2 \qquad (3)$$

for the contribution in the transverse isotropic plane, and sim ilarly

$$\frac{h^2}{2_k} \frac{2}{e^2} \frac{e^2}{e^2} d^3r = \frac{h^2}{6_k} \frac{2}{e^2}$$
(4)

for the relative m otion along the principal axis. To calculate the potential energy we use the same transform ation to spherical coordinates. The integrals over the radial variable and the azim uth angle are readily evaluated, leaving

$$\frac{e^{2}}{4_{0}} \frac{Z}{p} \frac{1}{\frac{x^{2} + y^{2} + z^{2}}{Z}} d^{3}r$$

$$= \frac{e^{2}}{8_{0}} \frac{p}{p} \frac{\sin d}{1 + (2 - 1)\cos^{2}} : (5)$$

The evaluation of the remaining integral over the polar angle depends on the sign of the factor ² 1. If > 1 we substitute t = $p \frac{1}{1} \frac{2}{2} 1 \cos r$, otherwise we use the substitution t = $p \frac{1}{1} \frac{2}{2} \cos r$ to obtain an elementary integral, which is solved by

$$I() = \frac{1}{2} \frac{\sum_{0}^{2} \frac{\sin d}{1 + (2 - 1)\cos^{2}}}{\sum_{0}^{2} \frac{\arcsin h}{p} \frac{p}{2} \frac{1}{1}} \text{ for } > 1$$
$$= \frac{p}{\frac{\arcsin h}{p} \frac{1}{2}} \frac{1}{1 - 2} \text{ for } < 1;$$
(6)

W hile we have to make this form all case distinction, we emphasize that the energy function is smooth, with both branches of I () approaching unity in the limit ! 1.

Collecting the kinetic and potential contributions, we thus obtain the expression

E (;) =
$$\frac{h^2}{6} = \frac{2}{2} + \frac{1}{2} = \frac{e^2}{40}$$
 I() (7)

for the ground state energy, which must be minimized with respect to the parameters and . The kinetic

term is quadratic in while the potential term is linear, so the respective partial derivative is readily performed. The condition @E = @ = 0 then yields a relation between the two parameters at the energy m inimum

$$= 3 \frac{e^2}{4_0} \frac{e^2}{h} \frac{2}{2} + \frac{1}{2_k} \frac{1}{k}$$
(8)

which, when substituted in (7), allows us to rewrite the energy as a function of only

E() =
$$\frac{3}{2} \frac{e^2}{4_0} h^2 \frac{2}{2} + \frac{1}{2_k} I^2$$
 (9)

The energy minimum is found at the stationary point for which @E = @ = 0 and through simple m athem atical rearrangement we can express this condition in the form

$$\frac{?}{k} = 2^{-3} \frac{1}{I()}$$
(10)

which may be solved graphically. The important point to note is that the right-hand side of (10) is a universal function f () that does not depend on the material properties, so the same plot can be used for all sem iconductors to determ ine . In practice, how ever, the reduced transverse and longitudinal e ective mass will offen not di er by more than a factor of three and in this value range the function on the right-hand side of (10) is accurately approximated by its low est-order polynom ial term f () ³. The parameter is then explicitly given by

$$=\frac{?}{k}^{1=3}$$
: (11)

This simpli cation allows for a very e cient analytic calculation of the material-speci c binding energy E_b , which is given by the modulus of the ground state energy according to (9). It is still exact in the isotropic lim it $_k = _2$, yielding the correct binding energy $E_b = R_1 m = (_2)^2$ where $R_1 = 13.6 \text{ eV}$ is the hydrogenic Rydberg energy. The wavefunction itself, required for instance to calculate the optical absorption $\cos -$ cient, is given by the original variational expression with de ned through the relation (8).

III.NUMERICAL RESULTS FOR GaN

In order to illustrate the numerical quality of our scheme, we now consider the case of gallium nitride as an explicit example for excitonic binding energies in a realistic sem iconductor. In G aN the valence band maximum comprises three alm ost degenerate subbands, giving rise to three distinct hole types that can partake in the form ation of excitons. C onventionally, these are referred to as light holes, heavy holes and split-o holes, re ecting their di erent e ective masses. W ithin the sam em aterial we can study excitons for which the reduced longitudinal

TABLE I. Comparison between approximate and numerically calculated binding energies $E_{\rm b}$ for excitons in GaN, formed with holes of dimented ective mass m $^{\rm h}$ from the three nearly degenerate subbands at the valence band maximum. The analytic approximation is accurate even when the anisotropy $_{\rm cl}$ = $_{\rm k}$ is very dimentify.

				Е _b (т	E _b (meV)	
H ole type	m ?	m k	_? = _k	approx.	num er.	
Light hole	0.15	1.10	0.483	15.456	15.458	
Heavy hole	1.65	1.10	0.959	24.809	24.809	
Split-o hole	1.10	0.15	1.805	18.939	18.941	

e ective mass is greater than the transverse as well as excitons for which it is smaller, and test the accuracy of the approximate treatment in either case.

The e ective mass of the electron at the bottom of the conduction band is $m_2^e = 0.18$ in the transverse and $m_{\nu}^{e} = 0.20$ in the longitudinal direction, given in units of the free electron m assm, while corresponding param eters for the three hole types are listed in table I. All values are quoted from [5]. Next the calculated anisotropy factors $_{2} = _{k}$ are given. For excitons form ed with heavy holes this is close to unity, indicating a rather small perturbation from the isotropic case, but the ratio is substantially smaller with light holes and larger with split-o holes, respectively. The fth column in table I lists the binding energies E_b obtained analytically from (9) with = $\binom{2}{2} = \binom{1}{k}^{1-3}$. These are compared with results that we obtained by exact diagonalization of the H am iltonian (1) using standard num erical techniques. The applicable value of the static dielectric constant is the low -frequency $\lim it = 9:5 \text{ of G aN}$.

The excellent agreem ent between the approxim ate and num erical results in all cases con m s the validity of the variationalwavefunction (2) as well as the accuracy of the additional simpli cation (11) that makes the approach strictly analytic. Com parison with experim ental data is more problem atic because it is very di cult to extract accurate binding energies from optical spectra. Neverthe less, the recently published values of 21 m eV for excitons with light and heavy holes and 23 m eV for excitons with split-o holes in GaN are probably quite reliable [6]. The discrepancy with the results obtained here is due to the underlying model H am iltonian (1), however, not the analytic approximations introduced to solve it. W hile the anisotropy in the e ective mass is treated adequately, other important features such as the mixing of states at the threefold degenerate valence band m axin um or the spatial variation of the dielectric function are still neglected. A more involved quantitative scheme will also have to incorporate these in order to reproduce experim ental binding energies for realm aterials.

ACKNOW LEDGEMENTS

The authorw ishes to thank T U enoyam a and M Suzuki for inspiration and hospitality at the Central Research Laboratories of M atsushita E lectric Industrial Co., Ltd. in the summer of 1996, and R W G odby for useful discussions. F inancial support from the D eutscher A kadem ischer A ustauschdienst under its H SP III scheme, the Studienstiftung des deutschen Volkes, the G ottlieb D aim lerund K arl B enz-Stiftung, Pem broke College C am bridge, the Engineering and P hysical Sciences Research C ouncil, and the Japan International Science and Technology E xchange C enter is gratefully acknow ledged.

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